



Standard Recovery Diodes (Stud Version), 12 A

FEATURES

- High surge current capability
- Stud cathode and stud anode version
- Wide current range
- Types up to 1200 V V_{RRM}
- · RoHS compliant
- Designed and qualified for industrial and consumer level

TYPICAL APPLICATIONS

- Battery charges
- Converters
- Power supplies
- Machine tool controls

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I _{F(AV)}		12	А		
	T _C	144	°C		
I _{F(RMS)}		19	А		
I _{FSM}	50 Hz	265	٨		
	60 Hz	280	А		
l ² t	50 Hz	351	A ² s		
	60 Hz	320	A-S		
V _{RRM}	Range	100 to 1200	V		
TJ		- 65 to 175	C°		

ELECTRICAL SPECIFICATIONS

PRODUCT SUMMARY

I_{F(AV)}

VOLTAGE RATINGS						
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	V _{R(BR)} , MINIMUM AVALANCHE VOLTAGE V ⁽¹⁾	I _{RRM} MAXIMUM AT T _J = 175 °C mA	
	10	100	150	-		
	20	200	275	-		
	40	400	500	500		
12F(R)	60	600	725	750	12	
	80	800	950	950		
	100	1000	1200	1150		
	120	1200	1400	1350		

Note

 $^{(1)}\,$ Avalanche version only available from $V_{\text{RRM}}\,400$ V to 1200 V







DO-203AA (DO-4)

12 A

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PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average forward current at case temperature	I _{F(AV)}	180° conduction, half sine wave		12 144	A °C	
Maximum RMS forward current	1=(=+++)			144	A	
	I _{F(RMS)}				19	A
Maximum on-repetitive peak reverse power	P _R ⁽¹⁾	10 μ s square pulse, T _J = T _J maximum		7	K/W	
		t = 10 ms	No voltage	Sinusoidal half wave, initial $T_J = T_J$ maximum	265	A
Maximum peak, one-cycle forward, non-repetitive surge current	I _{FSM}	t = 8.3 ms	reapplied		280	
		t = 10 ms	100 % V _{RRM} reapplied		225	
		t = 8.3 ms			235	
	l ² t	t = 10 ms	No voltage		351	A ² s
Maximum I ² t for fusing		t = 8.3 ms	reapplied		320	
		t = 10 ms	100 % V _{RRM}		250	
		t = 8.3 ms	reapplied		226	
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 to 10 ms, no voltage reapplied		3510	A²√s	
Low level value of threshold voltage	V _{F(TO)1}	(16.7 % x π x I _{F(AV)} < I < π x I _{F(AV)}), T _J = T _J maximum		0.77	v	
High level value of threshold voltage	V _{F(TO)2}	$(I > \pi x I_{F(AV)}), T_J = T_J maximum$		0.97	v	
Low level value of forward slope resistance	r _{f1}	(16.7 % x π x I _{F(AV)} < I < π x I _{F(AV)}), T _J = T _J maximum		10.70	m C	
High level value of forward slope resistance	r _{f2}	$(I > \pi x I_{F(AV)}), T_J = T_J maximum$		6.20	mΩ	
Maximum forward voltage drop	V _{FM}	$I_{pk} = 38 \text{ A}, T_J = 25 \text{ °C}, t_p = 400 \mu\text{s} \text{ rectangular wave}$		1.26	V	

Note

 $^{\left(1\right)}$ Available only for avalanche version, all other parameters the same as 12F

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction operating temperature range	TJ		- 65 to 175	°C	
Maximum storage temperature range	T _{Stg}		- 65 to 200		
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	2	K/W	
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, flat and greased		Γ\/ ¥¥	
		Not lubricated threads	1.5 + 0 - 10 %	N · m	
Allowable mounting targue		Not lublicated threads	13	lbf ⋅ in	
Allowable mounting torque		Lubricated threads	1.2 + 0 - 10 %	N · m	
		Lubricated infeads	10	lbf ⋅ in	
Approvimate weight			7	g	
Approximate weight			0.25	oz.	
Case style		See dimensions - link at the end of datasheet	DO-203AA (DO-4)		



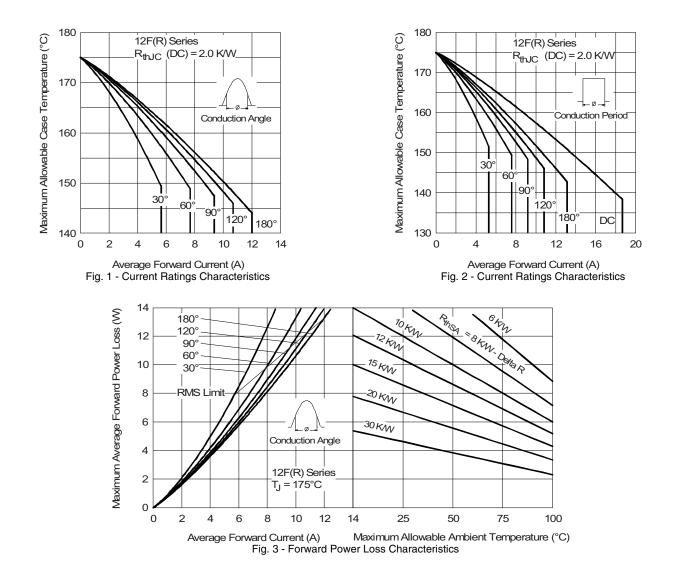
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CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS		
180°	0.33	0.26				
120°	0.41	0.44				
90°	0.53	0.58	$T_J = T_J maximum$	K/W		
60°	0.78	0.81				
30°	1.28	1.29				

Note

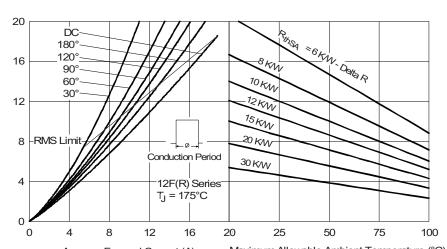
• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

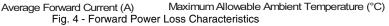


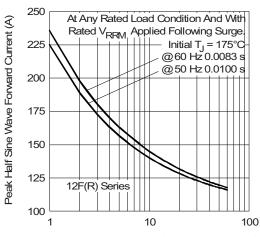
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Maximum Average Forward Power Loss (W)

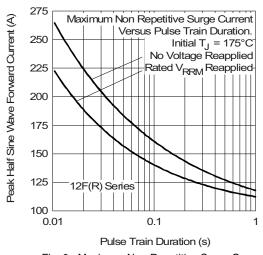




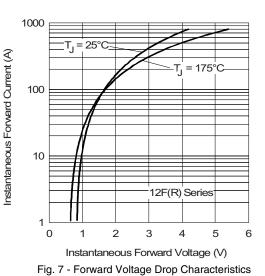




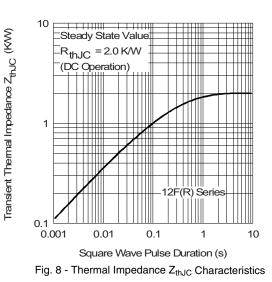








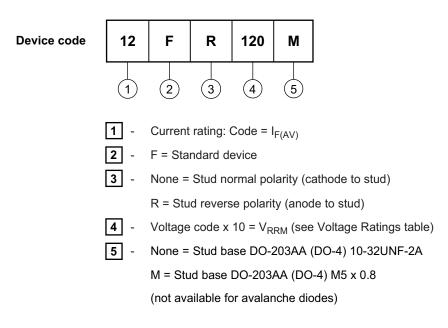
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ORDERING INFORMATION TABLE



LINKS TO RELATED DOCUMENTS		
Dimensions	http://www.vishay.com/doc?95311	



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R 0.40 R (0.02)

Ø 6.8 (0.27)

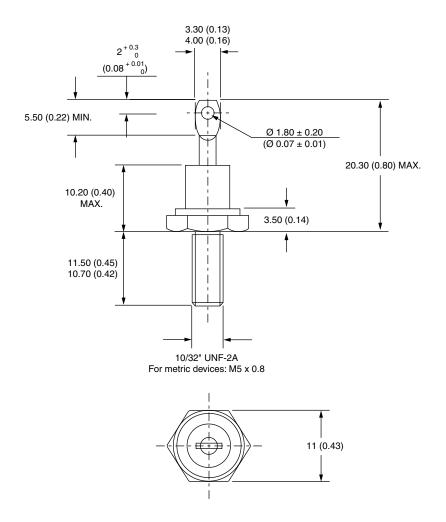
 0.8 ± 0.1

 (0.03 ± 0.004)



DO-203AA (DO-4)

DIMENSIONS in millimeters (inches)







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